

Wen-Hao Chang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

160
papers

6,977
citations

35
h-index

81
g-index

185
ext. papers

8,133
ext. citations

6.7
avg, IF

5.57
L-index

#	Paper	IF	Citations
160	Ultrafast multi-shot ablation and defect generation in monolayer transition metal dichalcogenides. <i>AIP Advances</i> , 2022 , 12, 015217	1.5	
159	In Situ Atomic-Scale Observation of Monolayer MoS ₂ Devices under High-Voltage Biasing via Transmission Electron Microscopy (Small 7/2022). <i>Small</i> , 2022 , 18, 2270034	11	
158	Ultrafast laser ablation, intrinsic threshold, and nanopatterning of monolayer molybdenum disulfide.. <i>Scientific Reports</i> , 2022 , 12, 6910	4.9	1
157	Room-Temperature Ferromagnetism of Single-Layer MoS ₂ Induced by Antiferromagnetic Proximity of Yttrium Iron Garnet. <i>Advanced Quantum Technologies</i> , 2021 , 4, 2000104	4.3	3
156	Atomic-Step-Induced Screw-Dislocation-Driven Spiral Growth of SnS. <i>Chemistry of Materials</i> , 2021 , 33, 186-194	9.6	4
155	Atomic-Layer Controlled Interfacial Band Engineering at Two-Dimensional Layered PtSe/Si Heterojunctions for Efficient Photoelectrochemical Hydrogen Production. <i>ACS Nano</i> , 2021 , 15, 4627-4635	16.7	12
154	Fabrication of Large-Scale High-Mobility Flexible Transparent Zinc Oxide Single Crystal Wafers. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 18991-18998	9.5	0
153	Momentum-Resolved Electronic Structures of a Monolayer-MoS ₂ /Multilayer-MoSe ₂ Heterostructure. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 16591-16597	3.8	1
152	High On-State Current in Chemical Vapor Deposited Monolayer MoS ₂ nFETs With Sn Ohmic Contacts. <i>IEEE Electron Device Letters</i> , 2021 , 42, 272-275	4.4	12
151	Strain-Directed Layer-By-Layer Epitaxy Toward van der Waals Homo- and Heterostructures 2021 , 3, 442-453		3
150	Time-resolved ARPES Determination of a Quasi-Particle Band Gap and Hot Electron Dynamics in Monolayer MoS. <i>Nano Letters</i> , 2021 , 21, 7363-7370	11.5	5
149	Purely in-plane ferroelectricity in monolayer SnS at room temperature. <i>Nature Communications</i> , 2020 , 11, 2428	17.4	88
148	Bidirectional All-Optical Synapses Based on a 2D Bi ₂ O ₂ Se/Graphene Hybrid Structure for Multifunctional Optoelectronics. <i>Advanced Functional Materials</i> , 2020 , 30, 2001598	15.6	48
147	Hybrid Composites of Quantum Dots, Monolayer WSe ₂ , and Ag Nanodisks for White Light-Emitting Diodes. <i>ACS Applied Nano Materials</i> , 2020 , 3, 6855-6862	5.6	3
146	Ultralow Schottky Barriers in Hexagonal Boron Nitride-Encapsulated Monolayer WSe Tunnel Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 18667-18673	9.5	10
145	Layer-Dependent and In-Plane Anisotropic Properties of Low-Temperature Synthesized Few-Layer PdSe Single Crystals. <i>ACS Nano</i> , 2020 , 14, 4963-4972	16.7	28
144	Wafer-scale single-crystal hexagonal boron nitride monolayers on Cu(111). <i>Nature</i> , 2020 , 579, 219-223	50.4	209

143	Nitride-stressor and quantum-size engineering in Ge quantum-dot photoluminescence wavelength and exciton lifetime. <i>Nano Futures</i> , 2020 , 4, 015001	3.6	2
142	Investigation of the spectral characteristics of silicon-vacancy centers in ultrananocrystalline diamond nanostructures and single crystalline diamond. <i>Journal of Applied Physics</i> , 2020 , 127, 035302	2.5	
141	Low temperature deposition of high quality single crystalline AlN thin films on sapphire using highly oriented monolayer MoS ₂ as a buffer layer. <i>Journal of Crystal Growth</i> , 2020 , 544, 125726	1.6	3
140	Moiré potential impedes interlayer exciton diffusion in van der Waals heterostructures. <i>Science Advances</i> , 2020 , 6,	14.3	29
139	Ledge-directed epitaxy of continuously self-aligned single-crystalline nanoribbons of transition metal dichalcogenides. <i>Nature Materials</i> , 2020 , 19, 1300-1306	27	41
138	Temperature-dependent optical and vibrational properties of PtSe thin films. <i>Scientific Reports</i> , 2020 , 10, 19003	4.9	8
137	2D Materials: Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter (Adv. Mater. 18/2019). <i>Advanced Materials</i> , 2019 , 31, 1970132	24	0
136	Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter. <i>Advanced Materials</i> , 2019 , 31, e1900861	24	28
135	Monolayer MoS ₂ Enabled Single-Crystalline Growth of AlN on Si(100) Using Low-Temperature Helicon Sputtering. <i>ACS Applied Nano Materials</i> , 2019 , 2, 1964-1969	5.6	15
134	Cross-plane thermoelectric figure of merit in graphene - C60 heterostructures at room temperature. <i>FlatChem</i> , 2019 , 14, 100089	5.1	4
133	Dielectric impact on exciton binding energy and quasiparticle bandgap in monolayer WS ₂ and WSe ₂ . <i>2D Materials</i> , 2019 , 6, 025028	5.9	25
132	Influences of Contact Metals on the Performances of MoS ₂ Devices under Strains. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 30696-30703	3.8	1
131	Tailoring excitonic states of van der Waals bilayers through stacking configuration, band alignment, and valley spin. <i>Science Advances</i> , 2019 , 5, eaax7407	14.3	31
130	Epitaxial Growth of Optically Thick, Single Crystalline Silver Films for Plasmonics. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 3189-3195	9.5	12
129	Distributed Bragg Reflectors as Broadband and Large-Area Platforms for Light-Coupling Enhancement in 2D Transition-Metal Dichalcogenides. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 16874-16880	9.5	11
128	Multidirection Piezoelectricity in Mono- and Multilayered Hexagonal HnSe. <i>ACS Nano</i> , 2018 , 12, 4976-4983	3.7	133
127	Negative circular polarization emissions from WSe ₂ /MoSe ₂ commensurate heterobilayers. <i>Nature Communications</i> , 2018 , 9, 1356	17.4	61
126	Three-Dimensional Resolvable Plasmonic Concentric Compound Lens: Approaching the Axial Resolution from Microscale to Nanoscale. <i>ACS Photonics</i> , 2018 , 5, 834-843	6.3	3

125	Atomic scale depletion region at one dimensional MoSe ₂ -WSe ₂ heterointerface. <i>Applied Physics Letters</i> , 2018 , 113, 241601	3.4	8
124	Efficient modulation of subwavelength focusing via meta-aperture-based plasmonic lens for multifunction applications. <i>Scientific Reports</i> , 2018 , 8, 13648	4.9	4
123	Room-Temperature Ferroelectricity in Hexagonally Layered Hn ₂ Se ₃ Nanoflakes down to the Monolayer Limit. <i>Advanced Functional Materials</i> , 2018 , 28, 1803738	15.6	127
122	Large-Area 2D Layered MoTe ₂ by Physical Vapor Deposition and Solid-Phase Crystallization in a Tellurium-Free Atmosphere. <i>Advanced Materials Interfaces</i> , 2017 , 4, 1700157	4.6	41
121	Low-Threshold Plasmonic Lasers on a Single-Crystalline Epitaxial Silver Platform at Telecom Wavelength. <i>ACS Photonics</i> , 2017 , 4, 1431-1439	6.3	22
120	Graphene-Au nanoparticle based vertical heterostructures: A novel route towards high-ZT Thermoelectric devices. <i>Nano Energy</i> , 2017 , 38, 385-391	17.1	19
119	Evidence of indirect gap in monolayer WSe. <i>Nature Communications</i> , 2017 , 8, 929	17.4	72
118	Band Alignment of 2D Transition Metal Dichalcogenide Heterojunctions. <i>Advanced Functional Materials</i> , 2017 , 27, 1603756	15.6	55
117	Original method of GaN and InGaN quantum dots formation on (0001)AlN surface by ammonia molecular beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012007	0.3	1
116	Synthesis of SiV-diamond particulates via the microwave plasma chemical deposition of ultrananocrystalline diamond on soda-lime glass fibers. <i>Materials Research Express</i> , 2016 , 3, 106205	1.7	2
115	Large-area few-layer MoS ₂ deposited by sputtering. <i>Materials Research Express</i> , 2016 , 3, 065007	1.7	28
114	Photoluminescence Enhancement and Structure Repairing of Monolayer MoSe ₂ by Hydrohalic Acid Treatment. <i>ACS Nano</i> , 2016 , 10, 1454-61	16.7	137
113	Effect of focused ion beam deposition induced contamination on the transport properties of nano devices. <i>Nanotechnology</i> , 2015 , 26, 055705	3.4	9
112	Designer germanium quantum dot phototransistor for near infrared optical detection and amplification. <i>Nanotechnology</i> , 2015 , 26, 055203	3.4	18
111	NANOELECTRONICS. Epitaxial growth of a monolayer WSe ₂ -MoS ₂ lateral p-n junction with an atomically sharp interface. <i>Science</i> , 2015 , 349, 524-8	33.3	811
110	Layered MoS ₂ grown on c-sapphire by pulsed laser deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 187-191	2.5	99
109	Design of multifold Ge/Si/Ge composite quantum-dot heterostructures for visible to near-infrared photodetection. <i>Optics Letters</i> , 2015 , 40, 2401-4	3	2
108	Grain size effect of monolayer MoS ₂ transistors characterized by second harmonic generation mapping 2015 ,		1

107	Optically initialized robust valley-polarized holes in monolayer WSe ₂ . <i>Nature Communications</i> , 2015 , 6, 8963	17.4	120
106	Diffraction-Unlimited Plasmonic Nanolaser. <i>Topics in Applied Physics</i> , 2015 , 357-359	0.5	
105	Synthesis and structure of two-dimensional transition-metal dichalcogenides. <i>MRS Bulletin</i> , 2015 , 40, 566-576	3.2	30
104	Effect of Electrode Shape on Impedance of Single HeLa Cell: A COMSOL Simulation. <i>BioMed Research International</i> , 2015 , 2015, 871603	3	4
103	Optical detection of anisotropic g-factor and nuclear spin polarization in a single CdTe quantum well. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 033003	1.4	1
102	Bandgap tunability at single-layer molybdenum disulphide grain boundaries. <i>Nature Communications</i> , 2015 , 6, 6298	17.4	291
101	Band gap-tunable molybdenum sulfide selenide monolayer alloy. <i>Small</i> , 2014 , 10, 2589-94	11	92
100	Second harmonic generation from artificially stacked transition metal dichalcogenide twisted bilayers. <i>ACS Nano</i> , 2014 , 8, 2951-8	16.7	294
99	Large-area synthesis of highly crystalline WSe ₂ monolayers and device applications. <i>ACS Nano</i> , 2014 , 8, 923-30	16.7	732
98	Waveguide based energy transfer with gold nanoclusters for detection of hydrogen peroxide. <i>RSC Advances</i> , 2014 , 4, 30392-30397	3.7	
97	Monolayer MoSe ₂ grown by chemical vapor deposition for fast photodetection. <i>ACS Nano</i> , 2014 , 8, 8582-8590	16.7	413
96	Spectroscopic signatures for interlayer coupling in MoS ₂ -WSe ₂ van der Waals stacking. <i>ACS Nano</i> , 2014 , 8, 9649-56	16.7	233
95	All-color plasmonic nanolasers with ultralow thresholds: autotuning mechanism for single-mode lasing. <i>Nano Letters</i> , 2014 , 14, 4381-8	11.5	168
94	Polymer-free patterning of graphene at sub-10-nm scale by low-energy repetitive electron beam. <i>Small</i> , 2014 , 10, 4778-84	11	11
93	Controllable Synthesis of Band-Gap-Tunable and Monolayer Transition-Metal Dichalcogenide Alloys. <i>Frontiers in Energy Research</i> , 2014 , 2,	3.8	70
92	Optical properties associated with strain relaxations in thick InGaN epitaxial films. <i>Optics Express</i> , 2014 , 22 Suppl 2, A416-24	3.3	13
91	Determination of s-d exchange coupling in GaMnN by time-resolved Kerr rotation spectroscopy. <i>Physical Review B</i> , 2014 , 90,	3.3	2
90	Stacking fault induced tunnel barrier in platelet graphite nanofiber. <i>Applied Physics Letters</i> , 2014 , 105, 103505	3.4	4

89	Suppressed piezoelectric polarization in single InGaN/GaN heterostructure nanowires. <i>Physical Review B</i> , 2013 , 88,	3.3	8
88	Growth of optical-quality, uniform In-rich InGaN films using two-heater metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2013 , 383, 106-111	1.6	9
87	Recombination dynamics and carrier lifetimes in highly mismatched ZnTeO alloys. <i>Applied Physics Letters</i> , 2013 , 103, 261905	3.4	8
86	Efficient energy transfer from InGaN quantum wells to Ag nanoparticles. <i>Physical Chemistry Chemical Physics</i> , 2013 , 15, 3618-22	3.6	8
85	Investigations on diamond nanostructuring of different morphologies by the reactive-ion etching process and their potential applications. <i>ACS Applied Materials & Interfaces</i> , 2013 , 5, 7439-49	9.5	32
84	In-Plane Gate Transistors for Photodetector Applications. <i>IEEE Electron Device Letters</i> , 2013 , 34, 780-782	4.4	4
83	Distance dependence of energy transfer from InGaN quantum wells to graphene oxide. <i>Optics Letters</i> , 2013 , 38, 2897-9	3	13
82	Memory device application of wide-channel in-plane gate transistors with type-II GaAsSb-capped InAs quantum dots. <i>Applied Physics Letters</i> , 2013 , 103, 143502	3.4	7
81	Band alignment tuning of InAs quantum dots with a thin AlGaAsSb capping layer. <i>Applied Physics Letters</i> , 2013 , 102, 173104	3.4	6
80	Analysis of electrode shape effect on single HeLa cell impedance using COMSOL simulation 2013 ,		2
79	Temperature-dependent decay dynamics in highly mismatched ZnSe _{1-x} Te _x alloy. <i>Applied Physics Letters</i> , 2012 , 100, 071912	3.4	2
78	Plasmonic nanolaser using epitaxially grown silver film. <i>Science</i> , 2012 , 337, 450-3	33.3	57 ¹
77	Effects of oxygen bonding on defective semiconducting and metallic single-walled carbon nanotube bundles. <i>Carbon</i> , 2012 , 50, 4619-4627	10.4	7
76	Growth of sparse arrays of narrow GaN nanorods hosting spectrally stable InGaN quantum disks. <i>Optics Express</i> , 2012 , 20, 16166	3.3	10
75	Optical properties of Mn in regrown GaN-based epitaxial layers. <i>Optical Materials Express</i> , 2012 , 2, 469	2.6	4
74	Energy transfer from InGaN quantum wells to Au nanoclusters via optical waveguiding. <i>Optics Express</i> , 2011 , 19 Suppl 2, A194-200	3.3	3
73	Linear photon up-conversion of 450 meV in InGaN/GaN multiple quantum wells via Mn-doped GaN intermediate band photodetection. <i>Optics Express</i> , 2011 , 19 Suppl 6, A1211-8	3.3	9
72	Effects of GaAsSb capping layer thickness on the optical properties of InAs quantum dots. <i>Applied Physics Letters</i> , 2011 , 99, 073108	3.4	24

71	Optical characterization of isoelectronic ZnSe δ Ox semiconductors. <i>Journal of Crystal Growth</i> , 2011 , 323, 122-126	1.6	2
70	Magneto-optical properties of ZnMnTe/ZnSe quantum dots. <i>Journal of Crystal Growth</i> , 2011 , 323, 380-382		1
69	Anticorrelation between the splitting and polarization of the exciton fine structure in single self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , 2011 , 83,	3.3	27
68	Stress tuning of strong and weak couplings between quantum dots and cavity modes in microdisk microcavities. <i>Physical Review B</i> , 2011 , 84,	3.3	14
67	Carrier dynamics in isoelectronic ZnSe δ Ox semiconductors. <i>Applied Physics Letters</i> , 2010 , 97, 041909	3.4	18
66	Anomalous diamagnetic shift for negative trions in single semiconductor quantum dots. <i>Physical Review B</i> , 2010 , 81,	3.3	18
65	Cathodoluminescence studies of GaAs nano-wires grown on shallow-trench-patterned Si. <i>Nanotechnology</i> , 2010 , 21, 465701	3.4	1
64	Optical fine structures of highly quantized InGaAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 2010 , 81,	3.3	18
63	Strong coupling of different cavity modes in photonic molecules formed by two adjacent microdisk microcavities. <i>Optics Express</i> , 2010 , 18, 23948-56	3.3	19
62	Growth and optical properties of high-density InN nanodots. <i>Journal of Crystal Growth</i> , 2010 , 312, 3209-3213		5
61	Impacts of coulomb interactions on the magnetic responses of excitonic complexes in single semiconductor nanostructures. <i>Nanoscale Research Letters</i> , 2010 , 5, 680-5	5	10
60	DC Characteristics of InAlAs/InGaAsSb/InGaAs Double Heterojunction Bipolar Transistors. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 3327-3332	2.9	4
59	Electron-hole symmetry breakings in optical fine structures of single self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1155-1158	3	
58	Tailoring of the Wave Function Overlaps and the Carrier Lifetimes in InAs/GaAs δ Sbx Type-II Quantum Dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 2524-2528	3	4
57	Origins of nonzero multiple photon emission probability from single quantum dots embedded in photonic crystal nanocavities. <i>Applied Physics Letters</i> , 2009 , 94, 163111	3.4	2
56	Effects of thermal annealing on the emission properties of type-II InAs/GaAsSb quantum dots. <i>Applied Physics Letters</i> , 2009 , 94, 053101	3.4	38
55	Recombination lifetimes in InN films studied by time-resolved excitation-correlation spectroscopy. <i>Physical Review B</i> , 2009 , 80,	3.3	7
54	The structural and optical properties of InN nanodots grown with various V/III ratios by metal-organic chemical vapor deposition. <i>Nanotechnology</i> , 2009 , 20, 295702	3.4	3

53	Size-dependent strain relaxation in InN islands grown on GaN by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2009 , 94, 063102	3-4	4
52	Exciton fine structures and energy transfer in single InGaAs quantum-dot molecules. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 860-863		
51	Time-resolved photoluminescence of type-II InAs/GaAs quantum dots covered by a thin GaAs _{1-x} Sb _x layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 1449-1452		3
50	Effect of donor-acceptor concentration ratios on nonradiative energy transfer in closely packed CdTe quantum dots. <i>Applied Physics Letters</i> , 2009 , 95, 133123	3-4	16
49	Optical Properties of Uncapped InN Nanodots Grown at Various Temperatures. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 031001	1-4	3
48	Impacts of structural asymmetry on the magnetic response of excitons and biexcitons in single self-assembled In(Ga)As quantum rings. <i>Physical Review B</i> , 2009 , 80,	3-3	27
47	Pressure-induced metallization and resonant Raman scattering in Zn _{1-x} Mn _x Te. <i>Journal of Applied Physics</i> , 2008 , 104, 013503	2-5	7
46	Diamagnetic response of exciton complexes in semiconductor quantum dots. <i>Physical Review Letters</i> , 2008 , 101, 267402	7-4	52
45	Time-resolved photoluminescence of isoelectronic traps in ZnSe _{1-x} Te _x semiconductor alloys. <i>Applied Physics Letters</i> , 2008 , 93, 241909	3-4	19
44	Nonresonant carrier transfer in single InGaAs/GaAs quantum dot molecules. <i>Physical Review B</i> , 2008 , 77,	3-3	13
43	Carrier dynamics of type-II InAs/GaAs quantum dots covered by a thin GaAs _{1-x} Sb _x layer. <i>Applied Physics Letters</i> , 2008 , 93, 033107	3-4	38
42	Effects of growth temperature on InN/GaN nanodots grown by metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2008 , 103, 104306	2-5	15
41	Structural and optical properties of indium-rich InGaN islands. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1702-1705		2
40	Structural and optical properties of InN/GaN nanodots grown by metalorganic chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3014-3016		2
39	Carrier gas effects on the SiGe quantum dots formation. <i>Applied Surface Science</i> , 2008 , 254, 6257-6260	6-7	1
38	Studies on the electronic and vibrational states of colloidal CdSe/ZnS quantum dots under high pressures. <i>Nanotechnology</i> , 2007 , 18, 185402	3-4	16
37	Single photon emission from an InGaAs quantum dot precisely positioned on a nanoplane. <i>Applied Physics Letters</i> , 2007 , 90, 073105	3-4	23
36	Effect of ZnSe partial capping on the ripening dynamics of CdSe quantum dots. <i>Applied Physics Letters</i> , 2007 , 90, 083116	3-4	2

35	Structural and optical properties of In-rich InGaN nanodots grown by metallo-organic chemical vapor deposition. <i>Nanotechnology</i> , 2007 , 18, 405305	3-4	7
34	Raman scattering of longitudinal-optical-phonon-plasmon coupling in Cl-doped ZnSe under high pressure. <i>Journal of Applied Physics</i> , 2007 , 102, 123510	2-5	5
33	Growth of low density InGaAs quantum dots for single photon sources by metallo-organic chemical vapour deposition. <i>Nanotechnology</i> , 2006 , 17, 512-515	3-4	10
32	Photoluminescence properties of self-assembled InN dots embedded in GaN grown by metal organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2006 , 88, 191913	3-4	51
31	Impacts of ammonia background flows on structural and photoluminescence properties of InN dots grown on GaN by flow-rate modulation epitaxy. <i>Applied Physics Letters</i> , 2006 , 89, 263117	3-4	17
30	Enhancing luminescence efficiency of InAs quantum dots at 1.5 μ m using a carrier blocking layer. <i>Applied Physics Letters</i> , 2006 , 89, 053110	3-4	7
29	Efficient single-photon sources based on low-density quantum dots in photonic-crystal nanocavities. <i>Physical Review Letters</i> , 2006 , 96, 117401	7-4	212
28	Electroreflectance studies of InAs quantum dots with In _x Ga _{1-x} As capping layer grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2005 , 86, 131917	3-4	21
27	Self-assembled free-standing colloidal crystals. <i>Nanotechnology</i> , 2005 , 16, 1440-1444	3-4	27
26	Optical control of the exciton charge states of single quantum dots via impurity levels. <i>Physical Review B</i> , 2005 , 72,	3-3	18
25	Optical emission from individual InGaAs quantum dots in single-defect photonic crystal nanocavity. <i>Journal of Applied Physics</i> , 2005 , 98, 034306	2-5	2
24	Enhanced light emission from InAs quantum dots in single-defect photonic crystal microcavities at room temperature. <i>Applied Physics Letters</i> , 2005 , 87, 071111	3-4	8
23	1.55 μ m emission from InAs quantum dots grown on GaAs. <i>Applied Physics Letters</i> , 2005 , 87, 151903	3-4	18
22	Electroreflectance study on the polarization field in InGaN/AlInGaN multiple quantum wells. <i>Applied Physics Letters</i> , 2004 , 84, 1114-1116	3-4	24
21	Room temperature 1.3 and 1.5 μ m electroluminescence from Si/Ge quantum dots (QDs)/Si multi-layers. <i>Applied Surface Science</i> , 2004 , 224, 165-169	6-7	5
20	Optical properties of stacked Ge/Si quantum dots with different spacer thickness grown by chemical vapor deposition. <i>Applied Surface Science</i> , 2004 , 224, 148-151	6-7	9
19	Heteroepitaxial growth of wurtzite InN films on Si(111) exhibiting strong near-infrared photoluminescence at room temperature. <i>Applied Physics Letters</i> , 2004 , 84, 3765-3767	3-4	123
18	Room-temperature electroluminescence at 1.3 and 1.5 μ m from Ge/Si self-assembled quantum dots. <i>Applied Physics Letters</i> , 2003 , 83, 2958-2960	3-4	53

17	Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. <i>Journal of Applied Physics</i> , 2003 , 94, 1753-1757	2.5	35
16	Effects of spacer thickness on optical properties of stacked Ge/Si quantum dots grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2003 , 93, 4999-5002	2.5	28
15	Scanning electron filling modulation reflectance of charged InGaAs self-assembled quantum dot. <i>Journal of Applied Physics</i> , 2002 , 91, 4399-4402	2.5	1
14	Hole emission processes in InAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 2002 , 66,	3.3	43
13	Direct measurement of piezoelectric field in In _{0.23} Ga _{0.77} N/GaN multiple quantum wells by electrotransmission spectroscopy. <i>Journal of Applied Physics</i> , 2002 , 91, 531	2.5	56
12	A Carrier Escape Study from InAs Self-Assembled Quantum Dots by Photocurrent Measurement. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 224, 85-88	1.3	6
11	Effects of Electric Field and Coulomb Interaction on the Interband Transitions of InAs Self-Assembled Quantum Dots: A Study by Modulation Reflectance Spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 224, 89-92	1.3	2
10	Quantum-confined Stark shift in electroreflectance of InAs/In _x Ga _{1-x} As self-assembled quantum dots. <i>Applied Physics Letters</i> , 2001 , 78, 1760-1762	3.4	33
9	Photocurrent studies of the carrier escape process from InAs self-assembled quantum dots. <i>Physical Review B</i> , 2000 , 62, 6959-6962	3.3	77
8	Electron distribution and level occupation in an ensemble of In _x Ga _{1-x} As/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 2000 , 62, 13040-13047	3.3	20
7	Tuning the energy levels of self-assembled InAs quantum dots by rapid thermal annealing. <i>Applied Physics Letters</i> , 2000 , 76, 691-693	3.4	72
6	Excitation Density and Temperature Dependent Photoluminescence of InGaAs Self-Assembled Quantum Dots. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 554-557	1.4	10
5	Electron-filling modulation reflectance in charged self-assembled In _x Ga _{1-x} As quantum dots. <i>Physical Review B</i> , 1999 , 60, R2189-R2192	3.3	17
4	Fast Fourier transformation of piezoreflectance in δ-doped GaAs. <i>Journal of Applied Physics</i> , 1998 , 84, 1074-1080	2.5	5
3	A study of the Franz-Keldysh oscillations in electromodulation reflectance of Si-delta-doped GaAs by a fast Fourier transformation. <i>Journal of Applied Physics</i> , 1998 , 83, 7873-7878	2.5	11
2	Two-dimensional solid-phase crystallization toward centimeter-scale monocrystalline layered MoTe ₂ via two-step annealing. <i>Journal of Materials Chemistry C</i> ,	7.1	3
1	Ultrafast Exciton Trapping and Exciton-Exciton Annihilation in Large-Area CVD-Grown Monolayer WS ₂ . <i>Journal of Physical Chemistry C</i> ,	3.8	5